## CLAIMS

1. A piezoelectric element including an upper electrode, a piezoelectric and/or electrostrictive material and a lower electrode, characterized in that the piezoelectric and/or electrostrictive material is a composite oxide constituted by ABO<sub>3</sub> as general formula and the piezoelectric and/or electrostrictive material has a twin crystal.

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- A piezoelectric element according to claim 1,
  wherein the twin crystal has a twin crystal plane selected from a group represented by {110}.
  - 3. A piezoelectric element according to claim 1, wherein the twin crystal has a twin crystal plane selected from a group represented by {100}.
- 4. A piezoelectric element according to claim 2, wherein the piezoelectric and/or electrostrictive material is a tetragonal crystal.
  - 5. A piezoelectric element according to claim 2, wherein the piezoelectric and/or electrostrictive material is a rhombic crystal.
  - 6. A piezoelectric element according to claim 2, wherein the piezoelectric and/or electrostrictive material is a rhombohedral crystal.
- A piezoelectric element according to claim 1,
  wherein the piezoelectric and/or electrostrictive
  material has a twin crystal rate from 0.001 to 1.0.
  - 8. A piezoelectric element according to claim 1,

wherein the piezoelectric and/or electrostrictive material has an orientation property.

a direction of at least an axis.

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- 9. A piezoelectric element according to claim 8, wherein the piezoelectric and/or electrostrictive material has an orientation rate of 99 % or higher in
- 10. A piezoelectric element according to claim 8, wherein the piezoelectric and/or electrostrictive material has a principal crystal plane, in contact with the upper electrode, of {100}.
- 11. A piezoelectric element according to claim 8, wherein the piezoelectric and/or electrostrictive material has a principal crystal plane, in contact with the upper electrode, of {111}.
- 12. A piezoelectric element according to claim 8, wherein the piezoelectric and/or electrostrictive material has a principal crystal plane, in contact with the upper electrode, of {110}.
- 13. A piezoelectric element according to claim 20 1, wherein the lower electrode and the piezoelectric and/or electrostrictive material are directly formed on the substrate.
  - 14. A piezoelectric element according to claim 13, wherein a layer including the piezoelectric and/or electrostrictive material is formed with a thickness of 1 to 10  $\mu m$ .
  - 15. A piezoelectric actuator employing a piezoelectric element according to claim 1.

16. An ink jet recording head employing a piezoelectric element according to claim 1.